

Abstract

The deposition of material (3) on a growth area (4) may be highly temperature-sensitive. In order to reduce temperature inhomogeneities on the growth area (4) of a substrate wafer (1), a thermal radiation absorption layer (2) is applied on a rear side (5) of the substrate wafer (1) lying opposite to the growth area (4). The thermal radiation absorption layer (2) exhibits good radiation absorption in the spectral range of a heating source. Since the deposition of semiconductor materials, in particular AlInGaN, may lead to (depending on the deposition temperature) different emission wavelengths of the deposited material, the use of a thermal radiation absorption layer (2) may produce a narrower emission wavelength distribution of the deposited material (3).

(Figure 1c)